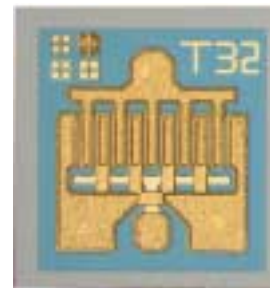


Low Noise and Medium Power GaAs FETs

FEATURES

- Low Noise Figure: NF = 0.8 dB Typical at 12 GHz
- High Associated Gain: Ga = 11 dB Typical at 12 GHz
- High Dynamic Range: 1 dB Compression Power $P_{1dB} = 24.5$ dBm at 12 GHz
- Breakdown Voltage: $BV_{DGO} \geq 9$ V
- $L_g = 0.25 \mu\text{m}$, $W_g = 600 \mu\text{m}$
- All-Gold Metallization for High Reliability
- Tight V_p ranges control
- High RF input power handling capability
- 100 % DC Tested

PHOTO ENLARGEMENT



DESCRIPTION

The TC1304 is a GaAs Pseudomorphic High Electron Mobility Transistor (PHEMT) chip, which has very low noise figure, high associated gain and high dynamic range. The device can be used in circuits up to 30 GHz and suitable for low noise and medium power amplifier applications including a wide range of commercial and military applications. All devices are 100% DC tested to assure consistent quality. All bond pads are gold plated for either thermo-compression or thermo-sonic wire bonding.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$)

Symbol	Conditions	MIN	TYP	MAX	UNIT
NF	Noise Figure at $V_{DS} = 4$ V, $I_{DS} = 50$ mA, $f = 12$ GHz		0.8	1.0	dB
G_a	Associated Gain at $V_{DS} = 4$ V, $I_{DS} = 50$ mA, $f = 12$ GHz	10	11		dB
P_{1dB}	Output Power at 1dB Gain Compression Point, $f = 12$ GHz, $V_{DS} = 6$ V, $I_{DS} = 80$ mA	23.5	24.5		dBm
G_L	Linear Power Gain, $f = 12$ GHz, $V_{DS} = 6$ V, $I_{DS} = 80$ mA	9	10		dB
I_{DSS}	Saturated Drain-Source Current at $V_{DS} = 2$ V, $V_{GS} = 0$ V		180		mA
g_m	Transconductance at $V_{DS} = 2$ V, $V_{GS} = 0$ V		200		mS
V_p	Pinch-off Voltage at $V_{DS} = 2$ V, $I_D = 1.2$ mA		-1.0*		Volts
BV_{DGO}	Drain-Gate Breakdown Voltage at $I_{DGO} = 0.3$ mA	9	12		Volts
R_{th}	Thermal Resistance		60		$^\circ\text{C}/\text{W}$

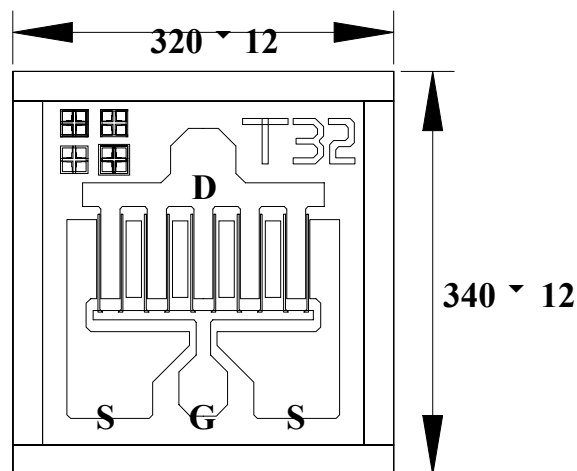
Note: * For the tight control of the pinch-off voltage. TC1304's are divided into 3 groups:

(1) **TC1304P0710** : $V_p = -0.7$ V to -1.0 V (2) **TC1304P0811** : $V_p = -0.8$ V to -1.1 V (3) **TC1304P0912** : $V_p = -0.9$ V to -1.2 V
 In addition, the customers may specify their requirements.

ABSOLUTE MAXIMUM RATINGS (T_A=25 °C) TYPICAL NOISE PARAMETERS (T_A=25 °C)
 $V_{DS} = 4 \text{ V}, I_{DS} = 50 \text{ mA}$

Symbol	Parameter	Rating
V _{DS}	Drain-Source Voltage	7.0 V
V _{GS}	Gate-Source Voltage	-3.0 V
I _{DS}	Drain Current	I _{DSS}
I _{GS}	Gate Current	600 μA
P _{in}	RF Input Power, CW	24 dBm
P _T	Continuous Dissipation	800 mW
T _{CH}	Channel Temperature	175 °C
T _{STG}	Storage Temperature	- 65 °C to +175 °C

Frequency (GHz)	NF _{opt} (dB)	G _A (dB)	Γ _{opt}		Rn/50
			MAG	ANG	
2	0.32	20.5	0.86	13	0.26
4	0.46	17.6	0.72	37	0.16
6	0.57	15.3	0.60	61	0.14
8	0.68	13.7	0.53	90	0.11
10	0.88	12.7	0.48	117	0.08
12	0.90	11.9	0.47	145	0.05
14	1.04	11.4	0.48	170	0.03
16	1.14	10.5	0.49	-166	0.03
18	1.25	9.8	0.52	-148	0.06

CHIP DIMENSIONS


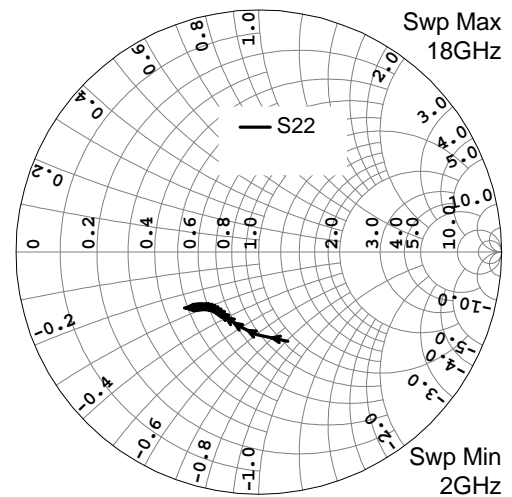
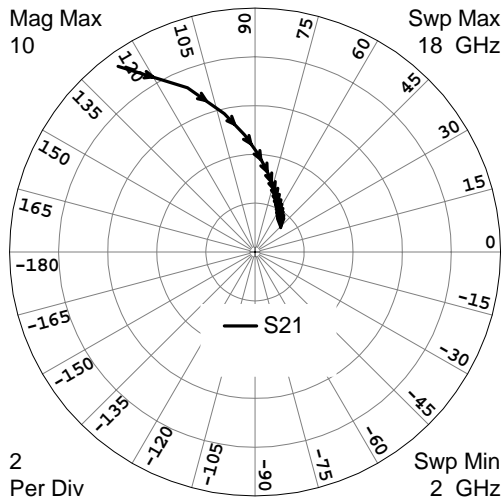
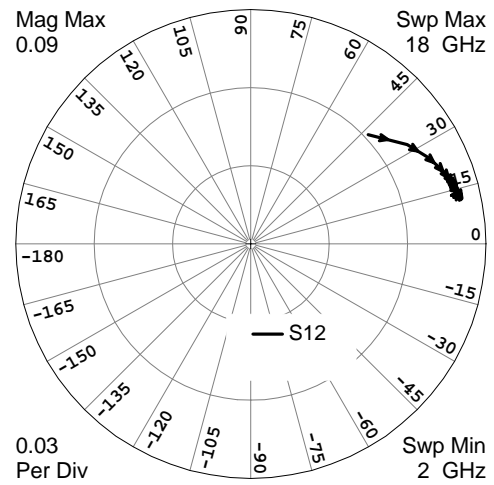
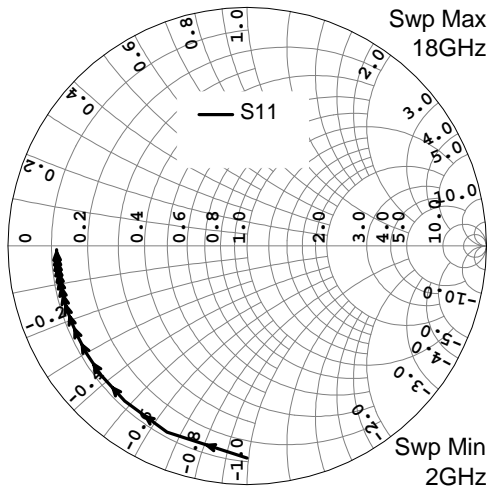
Units: Micrometers

Chip Thickness: 100

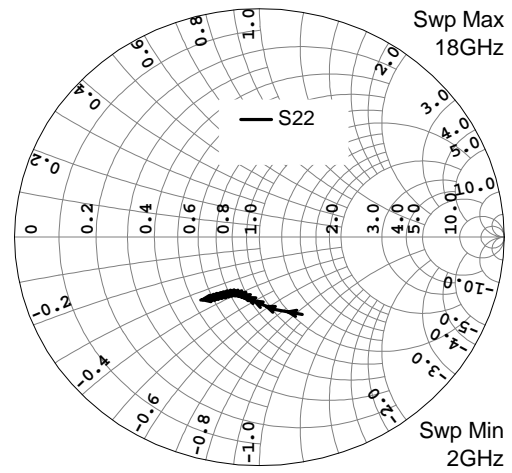
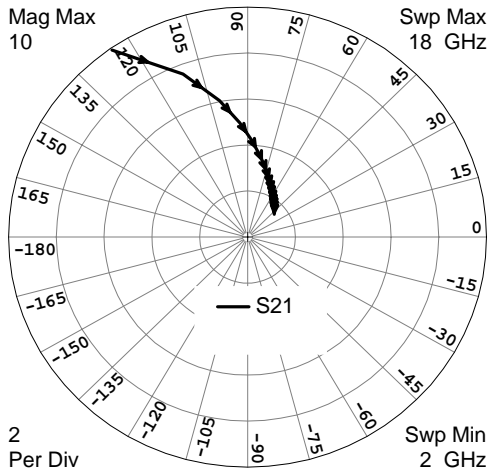
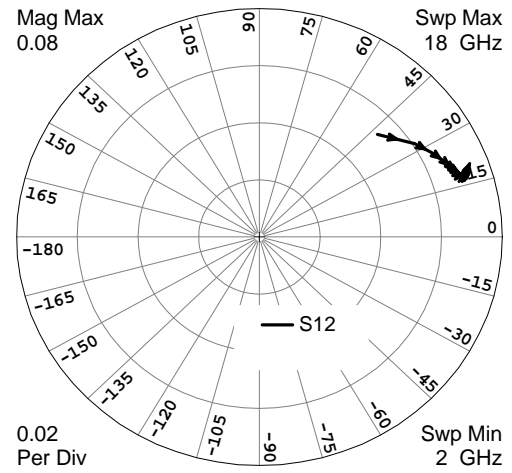
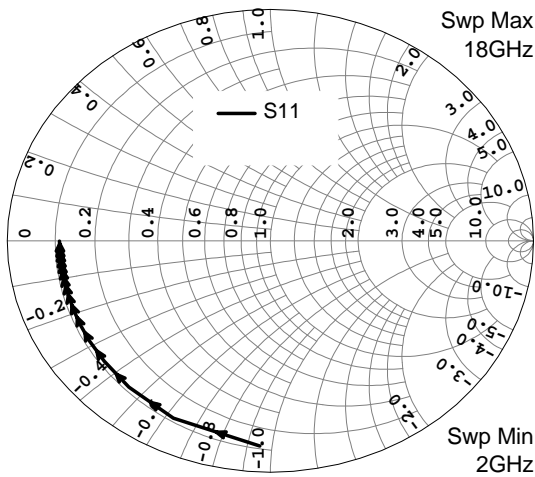
Gate Pad: 75 x 70

Drain Pad: 80 x 70

Source Pad: 75 x 80

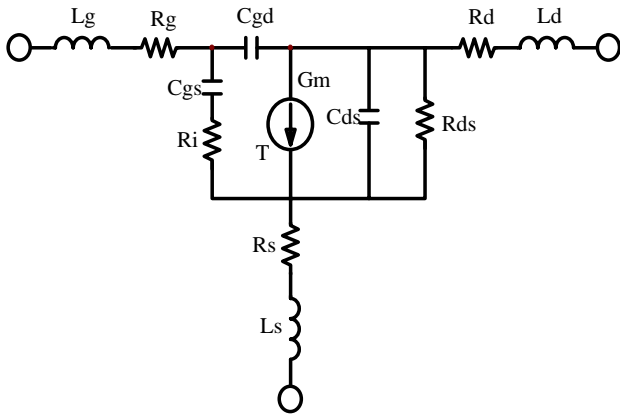
TYPICAL SCATTERING PARAMETERS (T_A=25 °C) V_{DS} = 4 V, I_{DS} = 50 mA


FREQUENCY (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
2	0.8898	-89.99	9.4335	126.22	0.0614	43.09	0.3867	-72.01
3	0.8498	-113.21	7.2703	112.17	0.0710	32.46	0.3415	-91.67
4	0.8279	-128.22	5.8073	102.40	0.0755	26.12	0.3169	-104.67
5	0.8155	-138.54	4.7993	94.95	0.0780	22.10	0.3045	-113.55
6	0.8082	-146.06	4.0762	88.85	0.0794	19.42	0.2993	-119.81
7	0.8036	-151.80	3.5371	83.59	0.0803	17.58	0.2986	-124.37
8	0.8006	-156.37	3.1217	78.89	0.0808	16.29	0.3009	-127.79
9	0.7986	-160.12	2.7927	74.57	0.0813	15.38	0.3052	-130.44
10	0.7974	-163.28	2.5263	70.54	0.0816	14.74	0.3111	-132.57
11	0.7966	-166.01	2.3063	66.73	0.0818	14.32	0.3181	-134.34
12	0.7962	-168.40	2.1218	63.08	0.0820	14.06	0.3260	-135.86
13	0.7960	-170.54	1.9648	59.58	0.0821	13.93	0.3346	-137.21
14	0.7960	-172.47	1.8297	56.19	0.0823	13.90	0.3438	-138.45
15	0.7961	-174.23	1.7122	52.90	0.0824	13.96	0.3534	-139.61
16	0.7964	-175.87	1.6091	49.69	0.0826	14.09	0.3634	-140.72
17	0.7968	-177.39	1.5178	46.56	0.0828	14.28	0.3737	-141.80
18	0.7972	-178.82	1.4364	43.50	0.0830	14.52	0.3842	-142.86

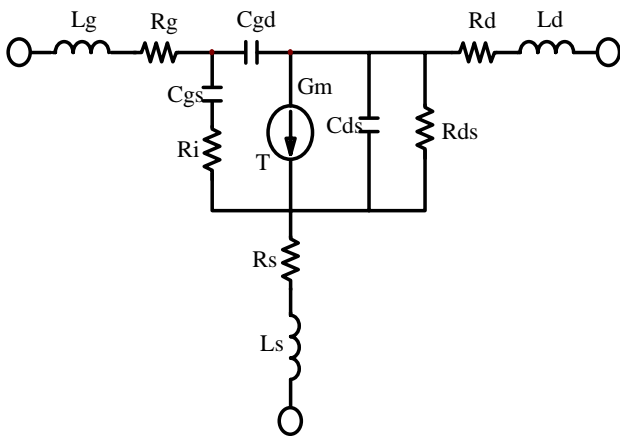
TYPICAL SCATTERING PARAMETERS (T_A=25 °C) V_{DS} = 6 V, I_{DS} = 80 mA


FREQUENCY (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
2	0.8887	-92.62	9.9171	124.88	0.0530	42.67	0.3809	-62.75
3	0.8506	-115.69	7.5873	110.88	0.0608	32.56	0.3220	-79.19
4	0.8304	-130.42	6.0381	101.19	0.0645	26.75	0.2893	-90.22
5	0.8190	-140.49	4.9806	93.79	0.0665	23.24	0.2725	-97.99
6	0.8123	-147.80	4.2262	87.71	0.0678	21.03	0.2653	-103.70
7	0.8081	-153.38	3.6657	82.44	0.0686	19.63	0.2641	-108.08
8	0.8054	-157.83	3.2350	77.72	0.0692	18.76	0.2668	-111.56
9	0.8036	-161.48	2.8946	73.38	0.0697	18.26	0.2723	-114.43
10	0.8024	-164.56	2.6194	69.31	0.0702	18.02	0.2795	-116.90
11	0.8016	-167.23	2.3926	65.45	0.0706	17.97	0.2882	-119.08
12	0.8011	-169.58	2.2027	61.76	0.0710	18.07	0.2978	-121.07
13	0.8009	-171.67	2.0414	58.21	0.0714	18.28	0.3081	-122.91
14	0.8008	-173.57	1.9028	54.76	0.0718	18.58	0.3189	-124.66
15	0.8008	-175.32	1.7825	51.41	0.0723	18.95	0.3301	-126.33
16	0.8009	-176.93	1.6770	48.14	0.0728	19.38	0.3416	-127.94
17	0.8012	-178.44	1.5839	44.94	0.0733	19.84	0.3532	-129.51
18	0.8015	-179.85	1.5011	41.81	0.0738	20.34	0.3649	-131.05

SMALL SIGNAL MODEL, V_{DS} = 4 V, I_{DS} = 50 mA

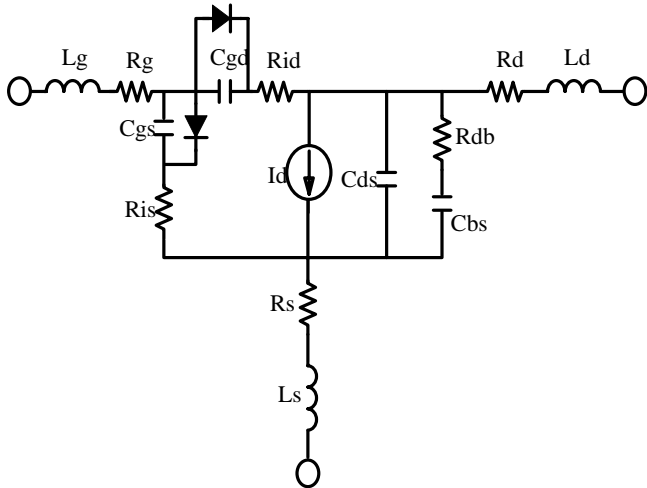
SCHEMATI

PARAMETERS

Lg	0.04 nH	Rs	1.5 Ohm
Rg	1.93 Ohm	Ls	0.01 nH
Cgs	1.1075 pF	Cds	0.15 pF
Ri	2.158 Ohm	Rds	105.4 Ohm
Cgd	0.087 pF	Rd	1.29 Ohm
Gm	266.7 mS	Ld	0.04 nH
T	3.6 psec		

SMALL SIGNAL MODEL, $V_{DS} = 6\text{ V}$, $I_{DS} = 80\text{ mA}$
SCHEMATI

PARAMETERS

Lg	0.04 nH	Rs	1.5 Ohm
Rg	1.93 Ohm	Ls	0.01 nH
Cgs	1.326 pF	Cds	0.137 pF
Ri	2.487 Ohm	Rds	111.5 Ohm
Cgd	0.072 pF	Rd	1.29 Ohm
Gm	287.3 mS	Ld	0.04 nH
T	4.64 psec		

LARGE SIGNAL MODEL, $V_{DS} = 6\text{ V}$, $I_{DS} = 80\text{ mA}$

SCHEMATIC

TOM2 MODEL PARAMETERS

Parameters		Parameters	
VTO	-0.393 V	VMAX	0.5 V
ALPHA	6.47	CGD	0.0754 pF
BETA	0.4622	CGS	6.18 pF
GAMMA	0.0394	CDS	0.1313 pF
DELTA	0.3935	RIS	2.2 Ohm
Q	0.78	RID	0.001 Ohm
NG	0.1	VBR	9 V
ND	0.01	RDB	120 Ohm
TAU	4.255 ps	CBS	0.042 pF
RG	1.2 Ohm	TNOM	25 °C
RD	1.29 Ohm	LS	0.01 nH
RS	1.594 Ohm	LG	0.041 nH
IS	1E-11 mA	LD	0.04 nH
N	1	AFAC	1
VBI	1 V	NFING	1
VDELTA	0.2 V		

CHIP HANDLING

DIE ATTACHMENT: Conductive epoxy or eutectic die attach is recommended. For eutectic die attach can be accomplished with Au-Sn (80%Au-20%Sn) perform in State Temperature: 290°C ± 5°C ; Handling Tool : Tweezers ; Time: less than 1min .

WIRE BONDING: The recommended wire bond method is thermo-compression bonding with 0.7 or 1.0 mil (0.018 or 0.025mm) gold wire. Stage Temperature: 220°C to 250°C ; Bond Tip Temperature : 150°C ; Bond Force: 20 to 30 gms depending on size of wire and Bond Tip Temperature.

HANDLING PRECAUTIONS: The user must operate in a clean, dry environment. Care should be exercised during handling avoid damage to the devices. Electrostatic Discharge (ESD) precautions should be observed at all stages of storage, handling, assembly, and testing. The static discharge must be less than 300V.